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## DECOMPOSITION STUDIES OF TRIISOPROPYLANTIMONY AND TRIALLYLANTIMONY

by

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Decomposition Studies of Triisopropylantimony and Triallylantimony

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#### Abstract

The pyrolysis of triisopropylantimony ((C3H7)3Sb) and triallylantimony ((C3H5)3Sb) has been investigated massspectrometrically in He and D2 using an SiO2 flow tube reactor at atmospheric pres ure. Both temperature and time dependencies of percent decomposition were studied and the reaction products were analyzed. The overall decomposition processes for both compounds were found to be homogeneous and first order. (C3H7)3Sb pyrolyzes at 250-350°C with no effect of the ambient gas. However, C3H6, C3H8, and C6H14 (2,3-dimethylbutane) were produced in He whereas C<sub>3</sub>H<sub>7</sub>D appeared in D<sub>2</sub>. The pyrolysis is believed to begin via bond cleavage to generate the free C3H7 radicals that, in turn, recombine and disproportionate. Isopropyl radicals react slowly with D2, producing the C3H7D detected. For (C3H5)3Sb, the pyrolysis takes place at 100-160°C. The only major product is C6H10 (1,5hexadiene). Both the pyrolysis rate and products were independent of the ambient. Two possible mechanisms, homolysis and reductive coupling, are discussed. Assuming that homolysis is the rate-limiting step for the pyrolysis of both (C3H7)3Sb and (C3H5)3Sb, bond strengths of 30.8 and 21.6 kcal/mole for C3H7—Sb and C3H5—Sb were determined from the experimental data. When either (C3H7)3Sb or (C3H5)3Sb was mixed with trimethylindium, a nonvolatile, liquid material, probably an adduct, was formed.

Keywords: triisopropylantimony, triallylantimony, pyrolysis, OMVPE.

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#### 1. Introduction

InSb and related alloys have direct bandgaps and extremely high intrinsic electron mobilities. This makes these materials attractive for both electronic and long-wavelength photonic devices. Quantum well/superlattice structures can be prepared using the organometallic vapor-phase epitaxy (OMVPE) technique [1]. However, these materials must be produced at relatively low temperatures. The melting point of InSb is only 524°C. At growth temperatures this low, the cost for a run may be macceptably high because the precursors, especially the commonly-used Sb precursor trimethylantimony ((CH3)3Sb), cannot efficiently decompose [2-4]. For example, InAsSbBi quaternary crystals need to be grown at approximetely 300°C [5] where the (CH3)3Sb decomposition percentage is less than 5% [2]. Therefore, more than 95% of the expensive source is wasted.

Efforts have recently been made to develop alternative, low-decomposition-temperature Sb precursors. Triisopropylantimony ((C3H7)3Sb) has been successfully used to grow InSb at temperatures as low as 300°C [6,7]. Such growth temperatures are difficult using (CH3)3Sb because of the slow pyrolysis rate. The capability for (C3H7)3Sb to grow materials at lower temperatures than those for (CH3)3Sb is a direct result of the lower bond strength of C3H7—Sb relative to CH3—Sb. The C3H7—H bond strength is 95.1 kcal/mole, significantly lower than that for CH3—H, 105.1 kcal/mole [8]. This bond strength/growth temperature relationship suggests that triallylantimony ((C3H5)3Sb) may allow even lower growth temperatures: The C3H5—H bond strength is only 86.3 kcal/mole [8].

In this work, the pyrolysis reactions for (C3H7)3Sb and (C3H5)3Sb have been investigated mass-spectrometrically in He and D2. The pyrolysis temperatures were measured, the products analyzed, and the reaction orders examined. The purpose of using D2 instead of H2 in this study is to label the pyrolysis products without appreciably altering the chemistry. This can resolve the role of H<sub>2</sub> in OMVPE growth. For some experiments, the reactor was packed to give a high surface area to determine whether the reaction is homogeneous or heterogeneous. A radical scavenger (1.4cyclohexadiene, C6H8) was also added to probe the role of free radicals in the pyrolysis process. Finally, each of the Sb precursors was mixed with trimethylindium ((CH<sub>3</sub>)<sub>3</sub>In) to study the In/Sb precursor interactions. The results of these studies provide important insights into the decomposition mechanisms. The information is useful for the design of Sb precursors and for the development of a low temperature OMVPE growth process for Sb-containing materials.

## 2. Experimental

The experiments were conducted in an isothermal, flow-tube, SiO2 reactor at atmospheric pressure (635 Torr in Salt Lake City). The diameter and the length of the reactor are 0.4 and 41.5 cm, respectively. The total gas flow rate was 40 sccm for the temperature dependence studies. However, for the time dependence studies, it was varied between 20-100 sccm. The effluent gas was sampled into a time-of-flight mass spectrometer via an adjustable leak. A schematic diagram of the apparatus has been pubished previously [9].

The synthesis of (C3H7)3Sb and (C3H5)3Sb was accomplished using the Schlenk techniques [10]. (C3H7)3Sb was prepared by the reaction of SbCl3 with C3H7MgCl in C4H8O [11]. (C3H5)3Sb was produced in a similar manner [12]. Colorless liquids were collected after filtration and precipitation. Subsequently, the liquids were purified by fractional vacuum distillation. Characterization was carried out by the <sup>1</sup>H and <sup>13</sup>C NMR spectroscopy. The vapor pressures at various temperatures were determined using a Hg manometer.

For the pyrolysis experiments, an ionization energy of 70 eV was used in the mass spectrometer. Mass spectra for (C3H7)3Sb and (C3H5)3Sb at room temperature were obtained first. Spectra for other reactants and products were acquired from the literature [13]. The ionization cross-sectional area for each molecule was assumed to be the sum of those of its constitutent atoms [14]. These procedures enabled the quantitative analysis of the percent decomposition and the concentrations of the reaction products. The mass spectrometer detectability limit was approximately 0.02%.

#### 3. Results

## 3.1 Vapor Pressures and Mass Spectra

The vapor pressures for (C3H7)3Sb and (C3H5)3Sb at different temperatures are listed in table 1. While they are low as compared to those for (CH3)3Sb and trivinylantimony ((C2H3)3Sb) [15], their room temperature vapor pressures are sufficient for OMVPE growth [7,16].

The relative intensities of the major mass-spectral peaks for (C3H7)3Sb and (C3H5)3Sb (0.05% in He for both) are shown in table

2. The principle peaks correspond to the C<sub>3</sub>H<sub>7</sub><sup>+</sup> and C<sub>3</sub>H<sub>5</sub><sup>+</sup> species for (C<sub>3</sub>H<sub>7</sub>)<sub>3</sub>Sb and (C<sub>3</sub>H<sub>5</sub>)<sub>3</sub>Sb, respectively. The parent peak of (C<sub>3</sub>H<sub>7</sub>)<sub>3</sub>Sb (molecular weight: 251) was monitored, whereas that for (C<sub>3</sub>H<sub>5</sub>)<sub>3</sub>Sb (molecular weight: 245) is undetectable, probably due to the very low bond strength of C<sub>3</sub>H<sub>5</sub>—Sb.

## 3.2. Effect of Ambient and Surface Area

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Using the peaks at m/e=251 for (C3H7)3Sb and m/e=204 for (C3H5)3Sb, the relative reactant concentrations at each temperature were determined. The temperature dependence of the percent decomposition under various conditions is plotted in Fig.1, for (C3H7)3Sb and (C3H5)3Sb, individually. The results for pyrolysis of (CH3)3Sb and (C2H3)3Sb in He are also shown for comparison [2,17]. A change of the ambient from He to D2 had no effect on the decomposition temperatures of either (C3H7)3Sb or (C3H5)3Sb. This indicates that either intramolecular reactions dominate or that free radicals produced do not react rapidly with D2. These results are similar to those reported previously for (C2H3)3Sb [17]; they are different from those for (CH3)3Sb. The presence of D2 has no apparent effect on the decomposition of (C2H3)3Sb [17], but D2 reduces the (CH3)3Sb decomposition temperature by more than 50° [2].

Increasing the surface area by a factor of 24 (the reactor was packed with SiO<sub>2</sub> chips with surface area determined by measuring the chip size) increases the decomposition rate slightly for (C<sub>3</sub>H<sub>7</sub>)<sub>3</sub>Sb and not at all for (C<sub>3</sub>H<sub>5</sub>)<sub>3</sub>Sb. The (C<sub>3</sub>H<sub>7</sub>)<sub>3</sub>Sb decomposition temperature was reduced by approximately 25°. Since a completely-heterogeneous reaction rate is proportional to the surface area, the

decomposition temperature for a 24-fold surface area can be calculated. The result is that the temperature should be decreased by 100° if an activation energy of 20 kcal/mole is assumed [18]. The pyrolysis processes for both precursors are believed to be mainly homogeneous. Homogeneous pyrolysis mechanisms have been also reported for (CH3)3Sb and (C2H3)3Sb [2,17].

## 3.3. Pyrolysis Products

The pyrolysis products for (C3H7)3Sb in He and D2 are given in Figs. 2a and 2b. The main products in He are C3H6, C3H8, and C6H14 (2,3-dimethylbutane). C3H6, C3H8, C6H14, and C3H7D were the products in D2. Although the effect of D2 on the decomposition rate was slight, the deuterated product C3H7D was found in D2. The same characteristics have been observed for triethylarsine ((C2H5)3As): D2 has no effect on the decomposition temperature, but C2H5D was produced [19]. These data suggest that the free C3H7 radicals produced from (C3H7)3Sb homolysis react slowly with D2 to produce C3H7D. The majority of the free C3H7 radicals recombine and disproportionate to form the C3H6, C3H8, and C6H14 observed. D atoms produced from the C3H7/D2 reaction play no important role in accelerating the (C3H7)3Sb decomposition.

The concentrations of the products C3H6 and C3H8 from disproportionation reaction are expected to be in a 1:1 ratio. However, more C3H6 than C3H8 was observed in both He and D2, as shown in Figs. 2a and 2b. This indicates the possibility of a parallel β-hydrogen elimination reaction. The β-hydrogen elimination reaction for (C3H7)3Sb may produce C3H6 and (C3H7)2SbH. The latter could not be detected in this study because its concentration was small and

the mass spectral peaks overlapped those of  $(C_3H_7)_3Sb$ . Competing homolysis and  $\beta$ -hydrogen elimination reactions have been proposed for the pyrolysis of the related compound disopropyltelluride  $((C_3H_7)_2Te)$  [20].

Figs. 3a and 3b display the pyrolysis products for (C3H5)3Sb in He and D2. The only detectable species was C6H10 (1,5-hexadiene) for both ambient gases. Obviously a C6H10 molecule can be formed by recombination of two C3H5 radicals. But, whether free radicals were existent during pyrolysis is unknown. C3H5 radicals may be too stable to react with D2, leading to the observation of no deuterated products.

In addition to the gaseous products discussed above, solid Sb deposits were observed in the reactor for both precursors. This combined with the observation of the insignificant effect of the surface area on the decomposition rates indicates that the Sb surface does not significantly catalyze the pyrolysis for either (C3H7)3Sb or (C3H5)3Sb.

#### 3.4. Reaction Order

The reaction order has been studied for the pyrolysis of both (C3H7)3Sb and (C3H5)3Sb. The time allowed for pyrolysis is varied by changing the total flow rate through the reactor tube, keeping the input reactant concentration constant. Figs. 4a and 4b are plots of -ln(I/I<sub>O</sub>) (first order assumption) and 1/I-1/I<sub>O</sub> (second order assumption) vs. reaction time [21]. I and I<sub>O</sub> denote the mass spectral intensities of the reactant at the output and input to the reactor. The reaction temperatures were fixed at 312 and 145°C for the pyrolysis of (C3H7)3Sb and (C3H5)3Sb, respectively. As seen in Fig.4a, the

relationship between  $-\ln(I/I_0)$  and time is linear. That for  $1/I-1/I_0$  and time is distinctly non-linear, since the data must pass through the origin [21]. The (C3H7)3Sb pyrolysis process is apparently first order. The  $-\ln(I/I_0)$  and  $1/I-1/I_0$  vs. time relationships in Fig.4b are similar. Thus, the (C3H5)3Sb pyrolysis process is also likely to be first order.

## 3.5. Effect of a Radical Scavenger

1,4-cyclohexadiene (C6H8) was used as a scavenger of both C3H7 and C3H5 radicals. It can effectively remove the C3H7 radicals yielding C3H8 and benzene [22]. Unfortunately, it is unknown whether C6H8 can completely scavenge C3H5 radicals. In general, C6H8 is believed to be more reactive than other scavengers such as benzene (C6H6) and toluene (C7H8) used to scavenge CH3 radicals for example [23]. C6H8 may decompose at temperatures above 400°C producing H radicals [24] complicating the interpretation of the data in some cases. However, this does not occur at the temperatures of <350°C used in this study.

It was found that addition of 2% C6H8 has no effect on the pyrolysis temperature of (C3H7)3Sb. However, the products, C6H14 and C3H7D, disappeared in both He and D2 ambients. This demonstrates the existence of free radicals during (C3H7)3Sb pyrolysis. The data clearly indicate that C3H7 radicals are not involved in the rate-determining reactions. They do not rapidly attack the parent molecule. Otherwise, the addition of C6H8 would increase the decomposition temperature.

Similarly, the addition of C6H8 was found to have no effect on (C3H5)3Sb pyrolysis. Both the decomposition temperature and the

product were unaffected in both He and D<sub>2</sub> ambients. These results may indicate that C<sub>6</sub>H<sub>8</sub> has little effect on C<sub>3</sub>H<sub>5</sub> radicals, which are considerably more stable than C<sub>3</sub>H<sub>7</sub> radicals. An alternate explaination is that there are no free radicals produced during pyrolysis. Similar findings were reported for diallyltelluride ((C<sub>3</sub>H<sub>5</sub>)<sub>2</sub>Te) pyrolysis [20]. C<sub>6</sub>H<sub>10</sub> was produced whether or not C<sub>6</sub>H<sub>8</sub> was added.

## 3.6. Effect of the Addition of (CH3)3In

To simulate OMVPE growth, (CH3)3In (0.03%) was mixed with (C3H7)3Sb and (C3H5)3Sb in separate experiments. Surprisingly, the (CH3)3In signal could not be detected. Transparent liquids, presumably low volatility adduct compounds, were condensed at the In/Sb manifold area upstream from the reactor. The manifold setup in these experiments is simply a 3 inch long Y-shaped quartz tube. This makes the precursor mixing time longer than that in a real OMVPE reactor. Parasitic reactions were not observed during the growth of InSb using these precursors [7,16].

#### 4. Discussion

## 4.1. (C3H7)3Sb Decomposition

The decomposition of (C3H7)3Sb is postulated to involve the following reactions:

(C3H7)3Sb	$\rightarrow$	$C_3H_7 + (C_3H_7)_2S_b$	(1)
(C3H7)2Sb	$\rightarrow$	$C_3H_7 + C_3H_7S_b$	(2)
C <sub>3</sub> H <sub>7</sub> S <sub>b</sub>	$\rightarrow$	$C_3H_7 + Sb$	(3)
2C3H7	<b>→</b>	C6H14	(4)
2C3H7	$\rightarrow$	$C_3H_6 + C_3H_8$ .	(5)
C3H7 + D2	<b>→</b>	C3H7D + D	(6)

 $2D \qquad \rightarrow \qquad D_2. \tag{7}$ 

 $(C_3H_7)_3Sb \rightarrow C_3H_6 + (C_3H_7)_2SbH.$  (8)

The rate-determining step is probably the first reaction. More radicals are released by reactions 2 and 3, resulting in Sb deposition. C3H7 radicals recombine and disproportionate (reactions 4 and 5) to form the products observed. For a D2 ambient, a fraction of the radicals will react with D2, producing C3H7D and D (reaction 6). No evidence of a reaction between D and (C3H7)3Sb was observed. The D atoms apparently recombine via reaction 7. The experimental results do not rule out reaction 8, the  $\beta$ -hydrogen elimination reaction. Although the trapping of C3H7 free radicals by C6H8 favors the homolysis mechanism, the observation of more C3H6 than C3H8 cannot be explained by reactions 1-7.

These pyrolysis pathways are different from those for (CH3)3Sb pyrolysis in D2. Although for both systems free radicals are produced and react with the D2 ambient, D atoms are much more important for the (CH3)3Sb pyrolysis process; the predominant product was CH3D and the decomposition rate was enhanced in D2 [2]. This can be understood in terms of the radical reactivity. The reactivity with D2 is in the order of CH3 >C2H5 >C3H7 [25].

## 4.2. (C3H5)3Sb Decomposition

Since the data are insufficient to uniquely define the mechanism, two schemes are discussed here.

## 1. Homolysis

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 $(C_3H_5)_3Sb \rightarrow C_3H_5 + (C_3H_5)_2Sb.$  (9)

## 2. Reductive Coupling

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$$(C_3H_5)_3Sb \rightarrow C_6H_{10} + C_3H_5Sb.$$
 (10)

Supplementary Reactions

$$(C_3H_5)_2Sb \rightarrow C_3H_5 + C_3H_5Sb$$
 (11)  
 $C_3H_5Sb \rightarrow C_3H_5 + Sb$  (12)  
 $2C_3H_5 \rightarrow C_6H_{10}$  (13)

Each scheme has something to recommend it. They are both consistent with the product (C6H<sub>10</sub>) and the homogeneous, first order nature of the overall reaction.

Homolysis has been proposed as the mechanism for pyrolysis of many group V organometallic molecules [2,17,19,26,27]. This reaction pathway, however, does not agree with the results of the free radical trapping experiment, unless C6H8 is unable to efficiently remove the C3H5 radicals from the system. Despite the fact that reductive coupling is considered to be unlikely for pyrolysis of main group organometallics [19], it has been proposed for the pyrolysis of tertiarybutylarsine (C4H9AsH2) [28] and (C2H3)3Sb [17]. It has also been suggested recently for pyrolysis of (C3H5)2Te [20]. Being intramolecular, reductive coupling would be unaffected by a radical trap.

Since the actual rate constant for the C<sub>3</sub>H<sub>5</sub>/C<sub>6</sub>H<sub>8</sub> reaction is unknown, it is speculative to draw any conclusions from the limited experimental data. Nevertheless, homolysis as the first step is plausible because of the extremely weak C<sub>3</sub>H<sub>5</sub>-Sb bond. Reductive coupling is not convincing in principle. Sb does not have an oxidation state of I and the reaction product C<sub>3</sub>H<sub>5</sub>Sb is not thermodynamically

stable. This kind of reaction is normally facilitated only if a lower oxidation state is available to allow the product to have a lower potential energy, a common situation for trasition metals [19,29].

## 4.3. Alkyl-Sb Bond Strengths

Assuming that the homolysis step limits the pyrolysis rates for both (C3H7)3Sb and (C3H5)3Sb, the alkyl-Sb bond strengths can be determined from the temperature dependence of the decomposition rate constants. The results are shown in the Arrhenius plots of Figs. 5a and 5b. The rate constant vs. temperature relationships can be expressed,

$$logk_1 (s^{-1})$$
 = 11.03 - 30.8 (kcal/mole)/2.303 RT (K) (15)  
 $logk_9 (s^{-1})$  = 10.50 - 21.6 (kcal/mole)/2.303 RT (K) (16)

for (C3H7)3Sb and (C3H5)3Sb, respectively. The activation energies indicate bond strengths which are significantly lower than those for CH3—Sb (62.3 kcal/mole) and C2H3—Sb (49.0 kcal/mole) [2,17].

## 4.4. Possibility of Adduct Formation

The use of low alkyl-metal bond-strength precursors for low temperature OMVPE has some potentially negative consequences. For example, the probability of forming adducts with the group III precursors, leading to unwanted parasitic reactions, may be increased. The stability of the Lewis acid/base adduct can be determined by estimating the strengths of the acid and base. The basicity of the group V precursors is reflected by the stability of the carbonium ion of the ligand groups. The more stable the carbonium ion, the more basic the precursor will be: As more electron density is shifted to the lone pair of the group V element, the precursor will be

more electron-donating. For example, stability of the carbonium ions is in the order CH3<sup>+</sup> <C2H5<sup>+</sup> <C4H9<sup>+</sup> [25]. The probability of the precursor forming an adduct with trimethylgallium ((CH<sub>3</sub>)<sub>3</sub>G<sub>a</sub>) increases as the group V precursor changes from trimethylarsine ((CH<sub>3</sub>)<sub>3</sub>A<sub>s</sub>) to (C<sub>2</sub>H<sub>5</sub>)<sub>3</sub>A<sub>s</sub> to tritertiarybutylarsine ((C<sub>4</sub>H<sub>9</sub>)<sub>3</sub>A<sub>s</sub>). This adduct formation trend, also applicable to (CH3)3In with Sb precursors, has been experimentally observed (assuming that the observed liquids represent the adducts) [30]. On the other hand, comparing the tri-, di-, and mono-alkyl precursors, the probability of forming an adduct (the liquid) with (CH3)3Ga is in the order (C<sub>2</sub>H<sub>5</sub>)<sub>3</sub>As >diethylarsine ((C<sub>2</sub>H<sub>5</sub>)<sub>2</sub>AsH) >monoethylarsine (C<sub>2</sub>H<sub>5</sub>A<sub>5</sub>H<sub>2</sub>) [31]. This is because the alkyl ligand delocalizes electrons more effectively than the H ligand [25]. Precursors with more alkyl ligands have higher lone pair electron densities. This makes these precursors more electron-donating and more likely to form an adduct.

Both C<sub>3</sub>H<sub>7</sub><sup>+</sup> and C<sub>3</sub>H<sub>5</sub><sup>+</sup> are stable carbonium ions, considering the low C<sub>3</sub>H<sub>7</sub>—H and C<sub>3</sub>H<sub>5</sub>—H bond strengths [25]. Thus, it is not surprising that the tri-alkyls (C<sub>3</sub>H<sub>7</sub>)<sub>3</sub>Sb and (C<sub>3</sub>H<sub>5</sub>)<sub>3</sub>Sb will likely form adducts with (CH<sub>3</sub>)<sub>3</sub>In.

#### 4.5. Use for OMVPE Growth

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The lower pyrolysis temperatures for (C3H7)3Sb and (C3H5)3Sb, as compared to those for (CH3)3Sb and (C2H3)3Sb, suggest that they are more suitable for low temperature OMVPE growth of Sb-containing materials. However, due to the possibility of adduct formation with the group III precursor, the reactor should be carefully designed to avoid parasitic reactions.

## 5. Summary

The pyrolysis reactions for (C3H7)3Sb and (C3H5)3Sb have been investigated in He and D2 ambients. (C3H7)3Sb and (C3H5)3Sb pyrolyze in the temperature ranges from 250 to 350°C and from 100 to 160°C, respectively. The ambient has no effect on the decomposition temperature of either precursor. For (C3H7)3Sb, a deuterated product, C3H7D, was produced in D2 in addition to the C<sub>3</sub>H<sub>6</sub>, C<sub>3</sub>H<sub>8</sub>, and C<sub>6</sub>H<sub>14</sub> (2,3-dimethylbutane) produced in He. For (C3H5)3Sb, the only major product is C6H10 (1,5-hexadiene) in both He and D2. The pyrolysis reactions for both precursors are homogeneous and first order. The addition of a radical scavenger C6H8 inhibited the formation of C3H7D and C6H14 in (C3H7)3Sb pyrolysis, but the C6H10 is still produced in (C3H5)3Sb pyrolysis. The (C3H7)3Sb decomposition probably begins via cleavage of the Sb-C bonds. However, for (C3H5)3Sb pyrolysis two possibilities, homolysis and reductive coupling, were proposed. Assuming that homolysis is the rate-determining step for both (C3H7)3Sb and (C3H5)3Sb, bond strengths of 30.8 and 21.6 kcal/mole for C3H7—Sb and C3H5—Sb, respectively, were suggested. When (CH3)3In was present, liquids, presumably adducts, between the In and Sb precursors were observed.

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## 7. References

- 1. G. B. Stringfellow, OMVPE, Theory and Practice, (Academic Press, Boston, 1989)
- 2. C. A. Larsen, S. H. Li, and G. B. Stringfellow, Chemistry of Materials, to be published.
- 3. K. Y. Ma, Z. M. Fang, D. H. Jaw, R. M. Cohen, G. B. Stringfellow, W. P. Kosar, and D. W. Brown, Appl. Phys. Lett. 55, 2420 (1989)
- 4. R. M. Biefeld, J. Crystal Growth, 75, 255 (1986)
- 5. K. Y. Ma and G. B. Stringfellow, unpublished results.
- 6. G. T. Stauf, D. K. Gaskill, N. Bottka, and R. W. Gedridge, Paper T5.6, MRS Meeting, Boston, Massachusetts, November, 1990.
- 7. C. H. Chen, G. B. Stringfellow, and R. W. Gedridge, Jr., OMVPE Work Shop, Panama City Beach, Florida, 1991.
- 8. T. H. Lowry and K. S. Richardson, Mechanism and Theory in Organic Chemistry, (3rd edition, Harper & Row, N. Y., 1987) p.747, chapter 9
- 9. N. I. Buchan, C. A. Larsen and G. B. Stringfellow, Appl. Phys. Lett., 51, 1024 (1987)
- 10. D. F. Shriver and M. A. Dredzon, The Manipulations of Air-Sensitive Compounds, (2nd ed., John Wiley & Sons, N. Y., 1986)
- 11. H. J. Breunig and W. Kanig, J. Organometallic Chem., C5, 186 (1980)
- 12. A. E. Borisov, N. V. Novikova, and A. N. Nesmeyanov, Izvest. Akad. Nauk SSSR, Ser. Khim., 1506 (1963); Chem. Abst. 59, 14021
- 13. F. W. McLafferty and D. B. Stauffer, The Wiley/NBS Registry of Mass Spectral Data, (Vol.1, John Wiley & Sons, N. Y., 1989)

- 14. J. W. Otvos and D. P. Stevenson, J. Am. Chem. Soc., 78, 546 (1956)
- 15. Data from CVD Metalorganics; L. Maier, D. Seyferth, F. G. A. Stone, and E. G. Rochow, J. Amer. Chem. Soc., 79, 5884 (1957)
- 16. C. H. Chen, private communication.
- C. A. Larsen, R. W. Gedridge, Jr., and G. B. Stringfellow,
   Chemistry of Materials, to be published; C. A. Larsen, R. W.
   Gedridge, Jr., S. H. Li, and G. B. Stringfellow, Paper E5.29, MRS
   Meeting, Boston, Massachusetts, November, 1990.
- 18. S. H. Li, unpublished data; chapter 4 of Ref.1.
- 19. P. W. Lee, T. R. Omstead, D. R. McKenna, and K. F. Jensen, J. Crystal Growth, 93, 134 (1988)
- 20. R. U. Kirss, D. W. Brown, K. T. Higa, and R. W. Gedridge, Jr., Organometallics, to be published.
- 21. O. Levenspiel, Chemical Reaction Engineering, 2nd.Edition, (John Wiley & Sons, Inc., N. Y., 1972) Chapter 2
- V. N. Konddratiev, Rate Constants of Gas Phase Reactions,
   (National Bureau of Standards, U. S. Depart. of Commerce,
   Washington, D. C., 1972) p.171
- 23. J. A. Kerr and M. J. Parsonage, Evaluated Kinetic Data on Gas
  Phase Hydrogen Transfer Reactions of Methyl Radicals,
  (Butterworths, London, 1976) p.76, p79, and p.80,
- 24. C. A. Larsen, S. H. Li, N. I. Buchan, and G. B. Stringfellow, J. Crystal Growth, 102, 126 (1990)
- 25. T. W. G. Solomons, Organic Chemistry, (John Wiley & Sons, Inc., N.Y., 1976) p.123, p.174

- 26. S. H. Li, C. A. Larsen, and G. B. Stringfellow, J. Crystal Growth, 102, 117 (1990)
- 27. S. H. Li, C. A. Larsen, and G. B. Stringfellow, J. Crystal Growth, to be published.
- 28. C. A. Larsen, N. I. Buchan, S. H. Li, and G. B. Stringfellow, J. Crystal Growth, 93, 15 (1988)
- G. Wilkinson, F. G. Stone, and E. W. Abel, Comprehensive
   Organometallic Chemistry, (Pergamon, Oxford, 1982) Chapter
   19
- 30. S. H. Li, unpublished data; (C4H9)3As has not been combined with TMGa, however, the combination of (C4H9)2AsH and (CH3)3Ga led to a stable liquid material. The combination of (C2H5)3As+(CH3)3Ga also led to a liquid material. But, the combination of (CH3)3As+(CH3)3Ga did not.
- 31. S. H. Li, C. A. Larsen, and G. B. Stringfellow, J. Electronic Materials, to be published.

## Captions

- Fig.1 Temperature dependence of percent decomposition for several Sb precursors: (C3H7)3Sb (TiPSb, 0.05%), (C3H5)3Sb (TASb, 0.05%), (CH3)3Sb (TMSb, 1%), and (C2H3)3Sb (TVSb, 1%). ( ) in He; ( ) in D2; ( ) in D2 with a high surface area.
- Fig.2 Pyrolysis products of 0.05% (C3H7)3Sb in (a) He and (b) D2.
- Fig.3 Pyrolysis products of 0.05% (C3H5)3Sb in (a) He and (b) D2.
- Fig.4  $-\ln(I/I_0)$  and  $1/I-1/I_0$  vs. reaction time: (a) (C3H7)3Sb in D2, 312°C; (b) (C3H5)3Sb in D2, 145°C.
- Fig.5 Temperature dependences of the pyrolysis rate constants for (a) (C3H7)3Sb and (b) (C3H5)3Sb.

Table 1. Vapor Pressures of (C3H7)3Sb and (C3H5)3Sb

(C3H7)3Sb		(C3H5)3Sb		
Temp.(°C)	V. P. (Torr)	Temp.(°C)	V. P. (Torr)	
30-31	0.7	31-32	0.35	
32-33	0.8	34-35	0.5	
3 4	0.6	45-46	1.0	
4 4	1.6	56	1.35	
53-54	2.5	61	1.5	
57-58	3.25	71	2.0 (Ref.12)	
59-60	4.0			
logP(Torr) = 9.268 - 2881/T(K)		logP(Torr) = 6.089 - 1973/T(K)		

Table 2. Major Mass Spectral Peaks (70 eV) for (C3H7)3Sb and (C3H5)3Sb

(C <sub>3</sub> H	[7)3Sb	(C <sub>3</sub> H	5)3Sb
m/e	Rel. %	m/e	Rel. %
43	100	4 1	100
165	61	3 9	68
4 1	47	67	56
167	3 6	163	56
251	22	82	50
39	22	204	44
4 5	22	137	14

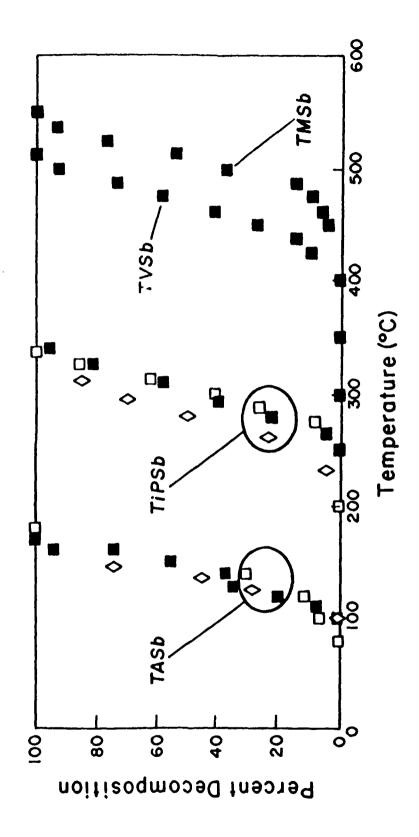
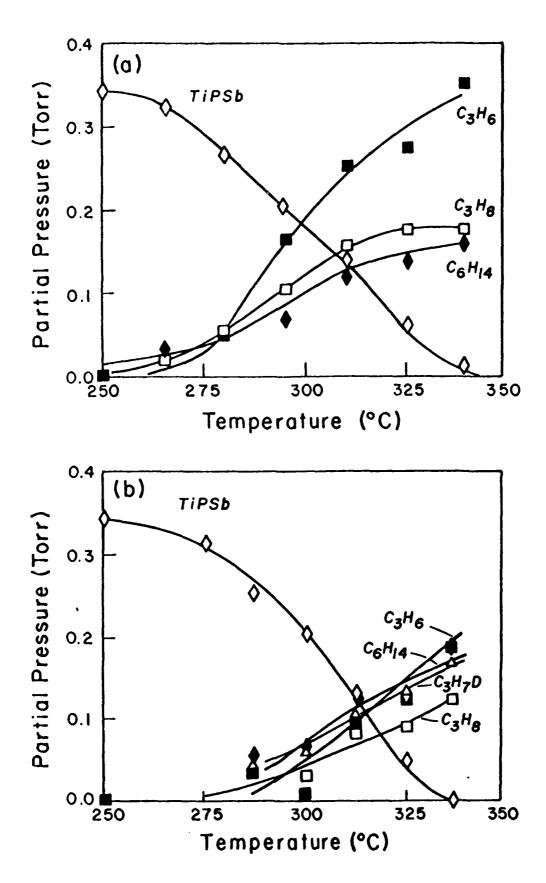
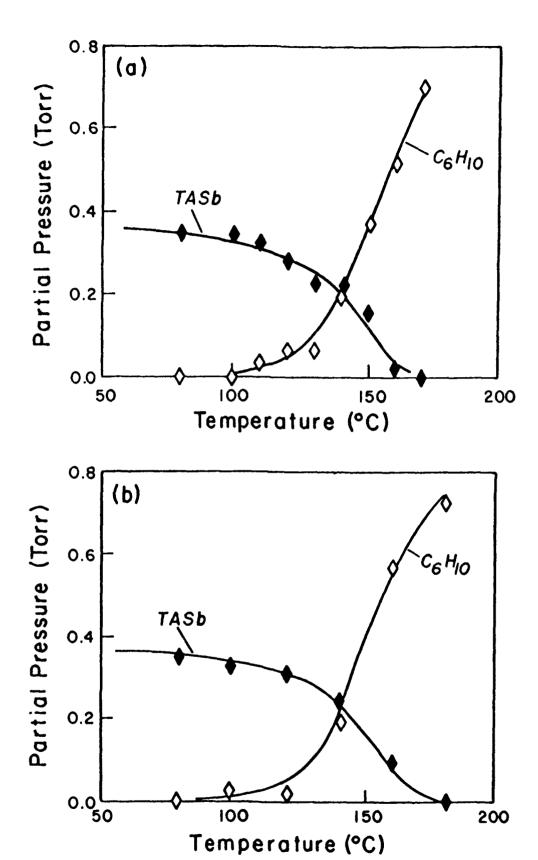


Fig.1





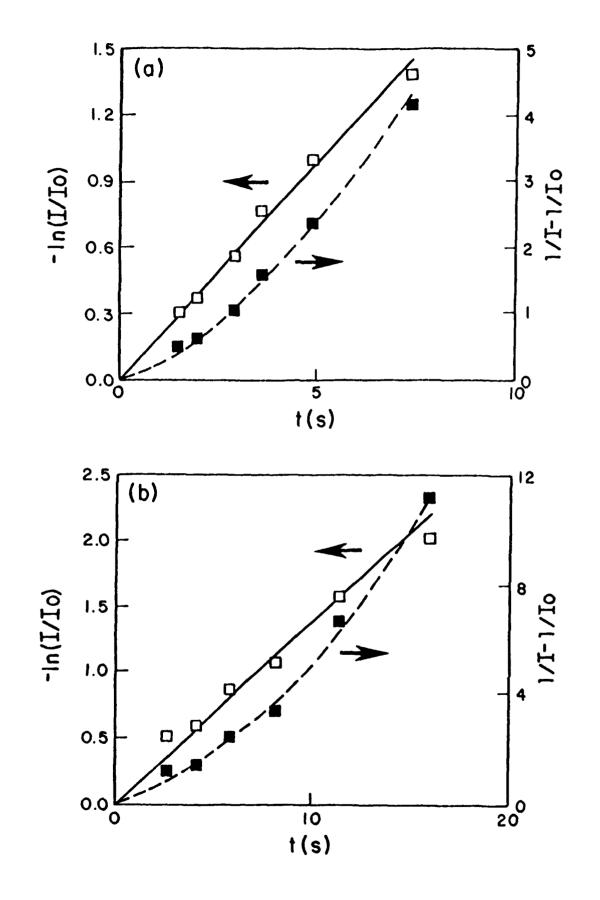
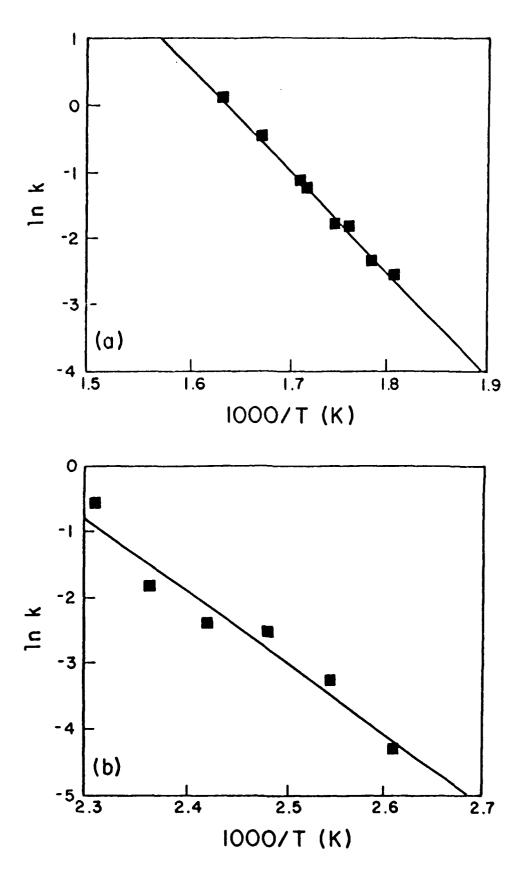


Fig 4



Fige